

## K<sub>2</sub>SO<sub>4</sub> nanowires a good nanostructured template

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### Abstract

K<sub>2</sub>SO<sub>4</sub> nanowires with the width of 66–100 nm were fabricated by ice-subliming method. Under the heat radiation, the surface of K<sub>2</sub>SO<sub>4</sub> nanowires presented ordering K<sub>2</sub>SO<sub>4</sub> dots of 3.5 nm and arrays of narrow wires with the width of 3 nm due to the remnant H<sub>2</sub>O molecules are released. Using these K<sub>2</sub>SO<sub>4</sub> nanowires as the substrate, ZnO nanowires were also fabricated by vapor-phase deposition.  
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### 1. Introduction

Progress in the fabrication and characterization of one-dimensional (1D) nanostructured materials has attracted much interest, owing both to their novel physical properties, which differ from those of bulk materials, and to their potential application in nanodevices [1–7]. Many methods succeed in fabricating nanowires and nanotubes such as metal catalysis [8], carbon nanotube template [9–11] and porous alumina template [12–15]. Because the template and catalysis should be removed for getting the pure 1D materials, it is important to find a template which can be easily removed. In this Letter, K<sub>2</sub>SO<sub>4</sub> nanowires template is introduced for its high melting point of 1362 K and being easily washed off. Specially, these K<sub>2</sub>SO<sub>4</sub> templates are more suitable to the vapor deposition method due to their loose structure permit the fabrication of the nanowires with different thickness or different materials. In addition, ordering QDs and narrow wires with size of several nanometers can form on the surface of K<sub>2</sub>SO<sub>4</sub> nanowires. Be-

cause ZnO is an *n*-type, direct band-gap semiconductor with  $E_g = 3.35$  eV [16,17] and particularly interesting for nanodevice applications, ZnO nanowires with ordering QDs is also fabricated.

### 2. Experimental

The fabrication of K<sub>2</sub>SO<sub>4</sub> nanowires by ice subliming method [18]: 0.251 g, 0.0251 g and 0.00251 g K<sub>2</sub>SO<sub>4</sub> with AR purity was dissolved in 50 ml water, respectively. After the solution of 0.5 wt% was filled into a 10 ml weighing bottle, it was immersed into liquid nitrogen (77 K). The ice containing K<sub>2</sub>SO<sub>4</sub> formed in a minute. Then the weighing bottle was placed into a vacuum chamber before liquid nitrogen had vaporized entirely. Finally the chamber was kept at about 10 Pa by being continually vacuumed with a steady rate of 4 L/s. After this lasted for 24 h, we got the residual white floccules. We also fabricated the products from the solution of 0.05 wt% and 0.005 wt% by the above process.

The fabrication of nanostructured ZnO on K<sub>2</sub>SO<sub>4</sub> nanowires: A molybdenum piece between the two electronic rods was used

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as the heat source. ZnO with 99.999% purity was placed on the molybdenum piece.  $K_2SO_4$  white floccules were placed on a copper net ( $\varnothing 3$  mm), 5 mm far away above ZnO source. The Mo piece was heated to 1373 K at  $1 \times 10^{-3}$  Pa. ZnO started to grow on  $K_2SO_4$  substrate. The growth process lasted for 30 minutes.

### 3. Results and discussion

The crystal structure of  $K_2SO_4$  product was characterized by X-ray diffraction (XRD). Fig. 1 is XRD spectrum of the products with the radiation of  $Cu K\alpha$ . The peaks show an orthorhombic structure with  $a = 5.770$  Å,  $b = 10.07$  Å and  $c = 7.477$  Å (PDF #830681). The morphology was characterized by transmission electron microscopy (TEM) with HITACHI TEM H-8100 IV at 200 kV. Fig. 2 shows the morphology of  $K_2SO_4$  product fabricated by ice subliming method. As shown in Fig. 2(a) (from 0.5 wt% solution), the structure is mainly composed of nanowires with the widths of 66–100 nm and some bridge junctions. Fig. 2(b) (from 0.05 wt% solution) and (c) (from 0.005 wt% solution) also show the nanowires with similar width, but they present more fractional segments.

We think the formation of the  $K_2SO_4$  nanowires as follows. When the sample temperature is very low (77 K), the sublimation rate of ice is also low, and the absorbed heat of the sample was larger than the heat loss induced by the sublimation of ice. This led to raise the sample temperature. The final temperature should balance the absorbed heat and the loss heat. The sublimation mainly progressed at this final temperature. The sample temperature in our experiments should be about 273 K for its permitting the high sublimation rate.

During the process of the sublimation, the pressure of the vacuum chamber kept at 10 Pa. It was far lower than the saturated vapor pressure of the ice at the experimental temperature.

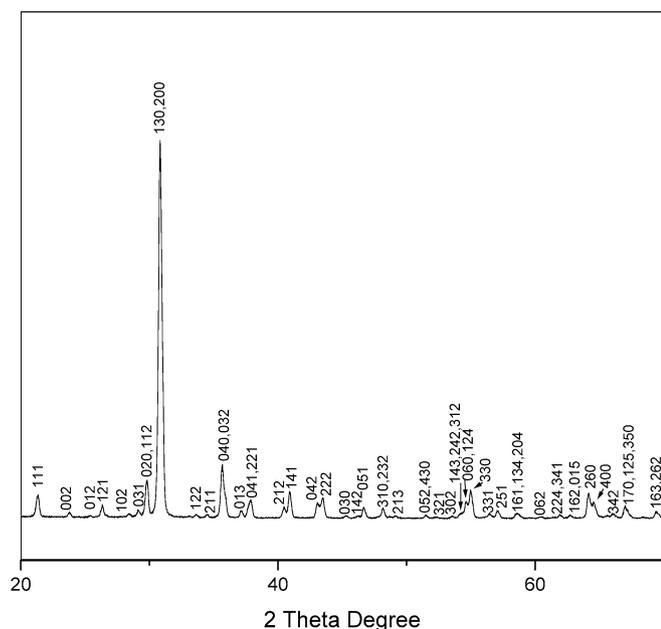


Fig. 1. XRD spectrum of  $K_2SO_4$  nanowires.

This showed that the process of the sublimation was mainly limited by the surface of the sample. That is to say, there was a need for increasing the surface area. Just this led to the spontaneously formation of the nanostructures of 66–100 nm for it can multiply the surface many times.

$K_2SO_4$  nanowires from the 0.5 wt%, 0.05 wt% and 0.005 wt%  $K_2SO_4$  solutions showed the nanowires with the similar width. So, we think the width of the  $K_2SO_4$  nanowires may be determined by the critical thickness with which the ice- $K_2SO_4$  layers were strong enough to support themselves.

We can image the formation of  $K_2SO_4$  nanowires. With the ice subliming, a groove first formed on the surface of the ice- $K_2SO_4$  layer, and the residual  $K_2SO_4$  are dusted on to the two edges. These  $K_2SO_4$  prevented the covered ice from subliming. And the nearest groove could only form on the other side of these residual  $K_2SO_4$  bars. When this process took place all over the surface, a spacing structure of  $K_2SO_4$  bar-groove formed. From Fig. 2(a), the groove can be validated by the white light strips on the middle of the nanowires with the width large than 100 nm. With the ice sublimation, the grooves were penetrated and  $K_2SO_4$  nanowires formed.

Because some  $H_2O$  may be embedded in  $K_2SO_4$  nanowires for a low fabrication temperature of about 273 K, the effect of electron radiation on the morphology of  $K_2SO_4$  nanowires was studied. When an electron beam with acceleration voltage of 200 kV and beam current of 15  $\mu A$  were projected on the  $K_2SO_4$  nanowires, some small holes formed on the surface of the wires. As shown in Fig. 3, these holes were not random but they were arranged in rows. This indicates that  $H_2O$  molecules were on the position of rows were easy to be picked off. The selective evaporation of  $H_2O$  molecules on the surface of  $K_2SO_4$  nanowires may be related with the crystal structure of  $K_2SO_4$  and heat conduction of the surface. Details research is undergoing.

With the increase of electron radiation, some ordered  $K_2SO_4$  dots form on the surface of  $K_2SO_4$  nanowires. As shown in Fig. 4, the even size of the dots is about 3.5 nm and the distance between two QDs is about 7.8 nm. With the further increase of electron radiation, as shown in Fig. 5, an array of narrow wires with diameter of about 3 nm can also form on the surface of  $K_2SO_4$  nanowires.

The formation of ordering QDs were explained as follows. When the  $K_2SO_4$  nanowires were under the electron radiation, the remnant  $H_2O$  molecules on the surface are heated and get rid off. This resulted in many vacancies appearing on the surface. The surface became instable. So it spontaneously formed  $K_2SO_4$  crystallites of about 3.5 nm. Now, the heat radiation could only get rid off the remnant  $H_2O$  molecules around the crystallites of about 3.5 nm. These new vacancies then compressed the crystallites to form a compact arrange, the ordered dots. When the dots were dense enough to be conterminous with the neighboring dots in a line, instead of separate crystallites the residual  $K_2SO_4$  formed narrow wires for the small crystallites being jointed with the neighboring ones. And the surface presented the narrow wires array.

The remnant  $H_2O$  molecules have been validated by the differential thermal analysis (DTA) measure on the fresh product.

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